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1N4447

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted) (Notes 1, 2, 3)

Symbol	Parameter Value		Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	100	V
I _{F(AV)}	Average Rectified Forward Current	200	mA
I _{FSM}	Non–repetitive Peak Forward Surge Current Pulse Width = 1.0 s Pulse Width = 1.0 μ s	1.0 4.0	A
T _{STG}	Storage Temperature Range	-65 to +200	°C
Τ _J	Operating Junction Temperature	175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are limiting values above which the serviceability of the diode may be impaired.
- 2. These ratings are based on a maximum junction temperature of 200°C.
- 3. These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
PD	Power Dissipation	500	mW
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	300	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

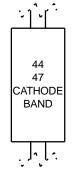
Symbol	Parameter	Test Conditions	Min	Max	Unit
V _R	Breakdown Voltage	I _R = 100 μA I _R = 5.0 μA	100 75	-	V
V _F	Forward Voltage	I _F = 20 mA	-	1.0	V
Ι _R	Reverse Leakage	$V_{R} = 20 V$ $V_{R} = 20 V$, $T_{A} = 150^{\circ}C$	-	25 50	nA μA
CT	Total Capacitance	V _R = 0, f = 1.0 MHz	-	2.0	pF
t _{rr}	Reverse Recovery Time	$\begin{array}{l} I_{\text{F}} = 10 \text{ mA}, V_{\text{R}} = 6.0 \text{ V} \\ I_{\text{rr}} = 1.0 \text{ mA}, \text{R}_{\text{L}} = 100 \Omega \end{array}$	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



CASE 017AG (Color Band Denotes Cathode)

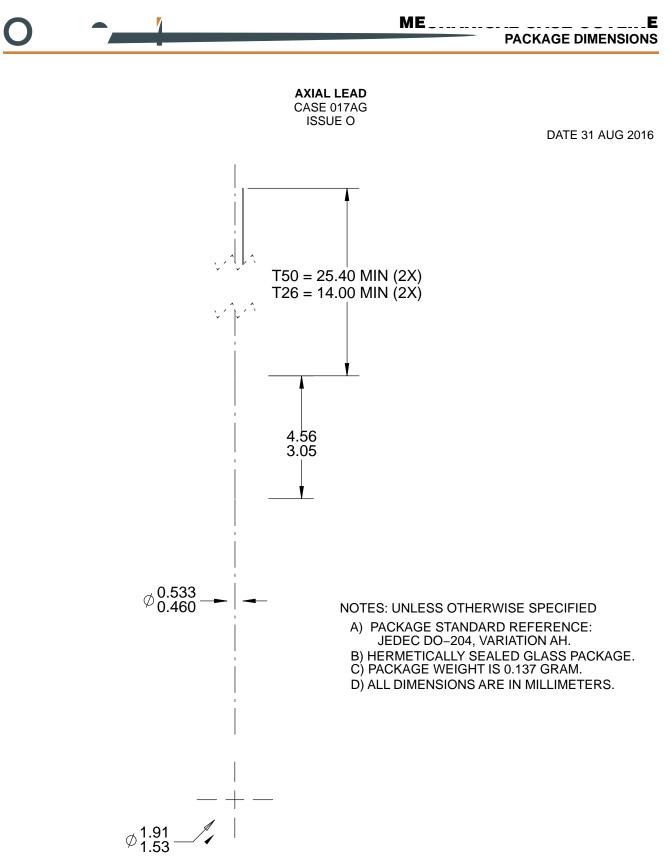
MARKING DIAGRAM



4447 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
1N4447	DO-35	5000 Units /
	(Pb–Free, Halide Free)	Bulk Bag



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